

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	288	(sige or gesi or silicon near germanium or si near ge) near6 (mbe or molecular adj beam adj epitaxy or mocvd or omvpe or uhvcvd or hvcvd or high near vacuum near2 cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 09:14
L3	25	(sige or gesi or silicon near germanium or si near ge) near6 (mocvd or omvpe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 09:14
L8	397	crystalliz\$ near3 anneal\$3 near20 (heating or (temperature or heat or temp or degree) near2 (ramp or ramping or increase or increasing or increased or up))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 09:35
L9	44	crystalliz\$ near3 anneal\$3 near4 (si or silicon or sige or gesi) near20 (heating or (temperature or heat or temp or degree) near2 (ramp or ramping or increase or increasing or increased or up))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 09:35
L11	191	438/509.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 10:01
L12	962	438/763.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 10:04
L13	28	438/763.ccls. and (strain or strained or straining or tensile or compressive or compressed) near2 (silicon or si)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 10:02
L14	151	438/938.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 11:20
L15	400	257/616.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 10:53
L17	333	257/E29.193.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 10:53
S1	349	(soi or sgoi or silicon-on-insulator) and (strained or straining or tensile) near3 (silicon or si) near8 (under or underneath or below or over or above or top or bottom or upon or higher or lower or underlying or overlying) near6 (sige or silicon near germanium or gesi or si near ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 09:01
S2	284	(soi or sgoi or silicon-on-insulator) near2 (strained or straining or tensile or compressed or compressive) near (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 09:00
S3	193	(ssoi or strained adj silicon-on-insulator or strained adj soi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 09:20
S4	2	"20020140031"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 09:20
S5	5	("5461250" "5759898" "6429061" "6593641" "6607948"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 10:23
S6	28	(hf or bhf or hydrofluoric) near4 (nitric) near6 (sige or gesi or silicon near germanium or si near ge)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 10:24

S7	151	(soi or sgoi or silicon-on-insulator) and (strained or straining or tensile) near3 (silicon or si) near8 (under or underneath or below or over or above or top or bottom or upon or higher or lower or underlying or overlying) near6 (sige or silicon near germanium or gesi or si near ge) and (etch\$4 or remov\$4) near3 (sige or gesi or si near ge or silicon near germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 11:16
S8	129	(soi or sgoi or silicon-on-insulator) and (strained or straining or tensile) near3 (silicon or si) near6 (sige or silicon near germanium or gesi or si near ge) and (straining or strained or strain or tensile) near6 (anneal or annealing or annealed)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:23
S9	8	(US-20020140031-\$ or US-20040142541-\$ or US-20040253792-\$ or US-20050124146-\$ or US-20050153524-\$ or US-20050167652-\$).did. or (US-6774015-\$).did. or (US-3272748-\$).did.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 16:48
S10	760	438/479.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/01 16:55
S11	56	438/479.ccls. and (strain or strained or straining or tensile or compressive or compressed) near2 (silicon or si)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 10:02
S12	323	438/481.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 09:44
S13	26	recrystal\$ near anneal\$3 near8 (temperature or heat or temp or degree) near2 (ramp or ramping or increase or increasing or increased)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/02 09:26
S14	4	"6825102".pn. "6774015".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 17:23